

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013

PHONE: (215) 631-9840 FAX: (215) 631-9855

MS1261

RF & MICROWAVE TRANSISTORS VHF MOBILE APPLICATIONS

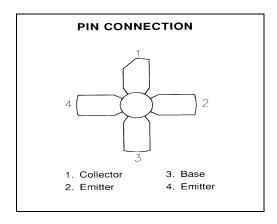
- Features
- 175 MHz
- 12.5 VOLTS
- P_{OUT} = 15 WATTS
- Gp = 12 dB MINIMUM
- INPUT IMPEDANCE MATCHING
- COMMON EMITTER CONFIGURATION

.280 4L STUD (M122) epoxy sealed

DESCRIPTION:

The MS1261 is a Class C 12.5V epitaxial silicon NPN planar transistor designed primarily for UHF communications. This devices utilizes a gold metallized, emitter ballasted die geometry for superior reliability and infinite VSWR capability.

www.DataSheet4U.com



ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
$V_{\sf CBO}$	Collector-Base Voltage	36	V
V_{CEO}	Collector-Emitter Voltage	18	V
V _{CES}	Collector-Emitter Voltage	36	V
V_{EBO}	Emitter-Base Voltage	4.0	V
Ic	Device Current	2.5	Α
P _{DISS}	Power Dissipation	34	W
Τ _J	Junction Temperature	+200	٥C
T _{STG}	Storage Temperature	-65 to +150	۰C

Thermal Data

P	Thermal Resistance Junction-case	g 75	°C/W
TH(J-C)	Thermal Nesistance Junction-case	0.73	C/VV



MS1261

ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC

Symbol	Test Conditions		Value			
		Min.	Тур.	Max.	Unit	
BV _{CES}	I _C = 50 mA	$V_{BE} = 0V$	36			V
BV _{CEO}	I _C = 15 mA		18			V
BV _{EBO}	I _E = 2.5 mA	$I_C = 0mA$	4.0			V
I _{CBO}	V _{CE} = 15 V	I _E = 0mA			1	mA
H _{FE}	V _{CE} = 5 V	I _C = 250mA	20		200	

DYNAMIC

Symbol	Test Conditions			Value		Unit	
Symbol			Min.	Тур.	Max.	Offic	
P _{out}	f = 175 MHz	P _{IN} = 1W	V _{CE} = 12.5V	15			W
ης	f = 175 MHz	$P_{IN} = 1W$	$V_{CE} = 12.5V$	60			%
G _P	f = 175 MHz	P _{IN} = 1W	V _{CE} = 12.5V	12			dB
Сов	f = 1 MHz	V _{CB} = 12.5V				45	pf

IMPEDANCE DATA

FREQ	$Z_IN(\Omega)$	$Z_{\mathtt{CL}}(\Omega)$
175 MHz	1.2 – j0.4	5.2 + j1.1

 $P_{OUT} = 15W$ $V_{CC} = 12.5V$





PACKAGE MECHANICAL DATA

